Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	791	(cascode or cascade) and (emitter with drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/11 10:10
L6	396	(pin) with emitter with control$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/11 10:14
L7	19	(cascode or cascade) and (pin with emitter with control$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/11 10:26
L8	111	(cascode or cascade) and ((pin or lead) with emitter with control$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/11 10:44
L10	564	(cascode or cascade) and pin and emitter and collector and gate and source and base	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/11 12:31
L11	1009	(pin or lead) with emitter with control$4 with (voltage or current)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/11 12:33
L12	179	(pin) with emitter with control$4 with (voltage or current)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/11 12:33
S1	2119	(257/723).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/07 09:29

S2	1683	(257/724).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/07 09:30
S3	1118	(438/107).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/07 09:29
S4	396	(438/110).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/07 10:35
S5	1	(dbc or "direct bonding" near2 copper) and MOS and bipolar and "power transistor" and cascode and (second near2 (die or device or transistor)) and pin near3 (fifth or five)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/07 10:40
S6	1	(dbc or "direct bonding" near2 copper) and MOS and bipolar and "power transistor" and cascode and (second near2 (die or device or transistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/07 10:40
S7	1	(dbc or "direct bonding" near2 copper) and MOS and bipolar and "power transistor" and cascode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/07 10:41
S8	9	(dbc or "direct bonding" near2 copper) and MOS and bipolar and cascode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/07 10:44
S9	123	(dbc or "direct bonding" near2 copper) and MOS and bipolar	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/07 11:05

S10	309	(MOS$3 or cmos!) and bipolar and cascode and pin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/07 11:14
S11	2	(MOS$3 or cmos!) and bipolar and cascode and pin and "lead?frame"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/07 11:15
S12	177	(MOS$3 or cmos!) and bipolar and cascode and pin and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/07 12:35
S13	33	cascode and (DBC or (direct adj bond$4 near3 copper))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/07 12:32
S14	227	(MOS$3 or cmos!) and cascode and pin and layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/07 12:58
S15	6	(("4768075") or ("5892279") or ("5942797")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/11 09:42
S16	4	("2583939").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/07 13:01
S17	16	("3935501" | "4218695" | "4492975" | "4514747" | "4547686" | "4571815" | "4639759" | "4649416" | "4651035" | "4663547").PN. OR ("4768075"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/07 14:16

S18	16	("3935501" | "4218695" | "4492975" | "4514747" | "4547686" | "4571815" | "4639759" | "4649416" | "4651035" | "4663547").PN. OR ("4768075"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/07 16:41
S19	335	(257/133).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/08 10:49
S20	1	S19 and (DBC or "direct bond$3")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/07 16:44
S21	384	(cmos or mosfet) and (DBC or "direct bond$3")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/07 16:46
S22	0	(cmos or mosfet) and ("direct bond$3")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 09:04
S23	757	(cmos or mosfet) and (direct near3 bond$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 09:05
S24	689	(cmos or mosfet) and (direct near2 bond$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 09:05
S25	244	(cmos or mosfet) and (direct near2 bond$3) and ceramic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 09:55

S26	4	(cmos or mosfet) and (direct near2 bond$3) and bi?polar	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 09:56
S27	689	(cmos or mosfet) and (direct near2 bond$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 09:56
S29	3	(cmos or mosfet or igmos) and (bi near2 polar or biploar or bi-polar) and (direct$2 near2 copper near2 bond$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 11:05
S30	9	(cascade or cascode) and (direct$2 near2 copper near2 bond$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 11:02
S32	57	(cmos or mosfet or igmos) and (bi near2 polar or biploar or bi-polar) and cascode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 11:03
S33	70	(cmos or mosfet or igmos) and (bi near2 polar or bipolar or bi-polar) and (direct$2 near2 copper near2 bond$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 11:22
S34	109	broich.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 14:45
S35	387	lead near2 frame and (bipolar or bi near2 polar or bi?polar or BJT) and collector	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 16:09

S36	1077	cascode and emitter and drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 16:09
S37	921	cascode and emitter and drain and control$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 16:11
S38	735	cascode and emitter and drain and control$4 and source and collector	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 16:11